



ABORN ELECTRONICS, INC.

T-41-85

Optically-Coupled Darlington Isolator

Optoelectronic Products

FCD860/C/D FCD865/C/D

General Description

The FCD860, FCD865 series of optoisolators have a silicon npn Planar Darlington phototransistor coupled to a GaAs diode. Each is mounted in a 6-pin plastic dual in-line package. The series was designed specifically as a high-sensitivity type for operation in the 1.0 mA input region.

Glassolated™

High Current Transfer Ratio at Low Input Current

1500 V to 6000 V Minimum Isolation

Input-to-Output

10^{11} Ω Isolation Resistance

Low Coupling Capacitance—Typically 1.5 pF

Absolute Maximum Ratings

Maximum Temperature and Humidity

Storage Temperature -55°C to $+150^{\circ}\text{C}$

Operating Temperature -55°C to $+100^{\circ}\text{C}$

Pin Temperature (Soldering, 10 s) 260°C

Total Package Power Dissipation

at $T_A = 25^{\circ}\text{C}$

(LED plus Detector) 250 mW

Derate Linearly from 25°C $3.3 \text{ mW}/^{\circ}\text{C}$

Input Diode

V_R Reverse Voltage 3.0 V

I_F Forward dc Current 80 mA

I_{pk} Peak Forward Current
($1 \mu\text{s}$ pulse width,
300 pps) 3.0 A

P_D Power Dissipation
at $T_A = 25^{\circ}\text{C}$ 150 mW
Derate Linearly from 25°C $2.0 \text{ mW}/^{\circ}\text{C}$

Output Transistor (Darlington)

V_{CE} Collector-to-Emitter

Voltage 30 V

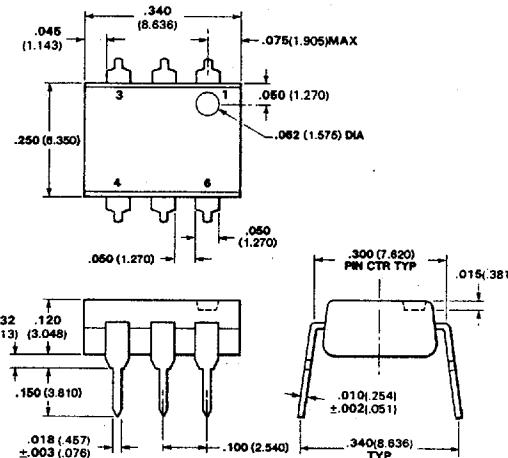
V_{CB} Collector-to-Base Voltage 30 V

V_{EC} Emitter-to-Collector

Voltage 7.0 V

P_D Power Dissipation
at $T_A = 25^{\circ}\text{C}$
($I_C(\text{max}) 100 \text{ mA}$
at $V_{CE} = 1.5 \text{ V}$) 150 mW
Derate Linearly from 25°C $2.0 \text{ mW}/^{\circ}\text{C}$

Package Outline

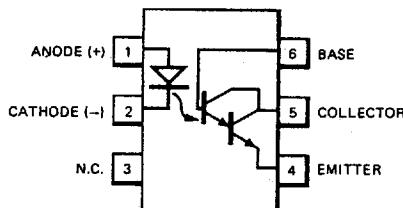


Notes

All dimensions in inches bold and millimeters (parentheses)

Tolerance unless specified = $\pm .015$ ($\pm .381$)

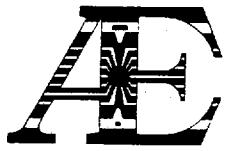
Connection Diagram DIP (Top View)



Pin

1	Anode (+)	Input Diode
2	Cathode (-)	
3	NC	
4	Emitter	Output npn Phototransistor
5	Collector	
6	Base	

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Typical Electrical Characteristics

FCD860/C/D
FCD865/C/D

Electrical Characteristics—Input Diode $T_A = 25^\circ\text{C}$

Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
V_F	Forward Voltage	3.0	1.25	1.5	V	$I_F = 20 \text{ mA}$
BV_R	Reverse Breakdown Voltage		5.0		V	$I_R = 10 \mu\text{A}$
C	Capacitance		150		pF	$V_R = 0 \text{ V},$ $f = 1 \text{ MHz}$

Electrical Characteristics—Output Transistor $T_A = 25^\circ\text{C}$ (Darlington)

Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
V_{CEO}	Collector-to-Emitter Voltage	30			V	$I_C = 1.0 \text{ mA},$ $I_F = 0$
V_{CBO}	Collector-to-Base Voltage	30			V	$I_C = 10 \mu\text{A},$ $I_F = 0$
V_{ECO}	Emitter-to-Collector Voltage	7.0			V	$I_E = 100 \mu\text{A},$ $I_F = 0$
V_{EBO}	Emitter-to-Base Voltage	6.0	8.0		V	$I_E = 100 \mu\text{A},$ $I_F = 0$
I_{CEO}	Collector-to-Emitter Leakage Current			100	nA	$V_{CE} = 10 \text{ V},$ $I_F = 0$
h_{FE}	Forward Current Gain		20 k			$V_{CE} = 5.0 \text{ V},$ $I_C = 25 \text{ mA}$

Electrical Characteristics—Coupled $T_A = 25^\circ\text{C}$

Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
V_{IO}	Input-to-Output Voltage (Note 1) FCD860, FCD865 FCD860C, FCD865C FCD860D, FCD865D	1500 5000 6000			V_{rms} V_{pk} V_{pk} V	
$V_{CE(sat)}$	Collector-to-Emitter Saturation Voltage			1.0	V	$I_C = 4.0 \text{ mA},$ $I_F = 2.0 \text{ mA}$
I_C	Collector Output Current FCD860, FCD860C FCD865, FCD865C	4.0			mA	$V_{CE} = 1.0 \text{ V},$ $I_F = 2.0 \text{ mA}$
R_{IO} C_{IO}	Input-to-Output Resistance Input-to-Output Capacitance		10^{11} 1.5		Ω pF	$V_{CE} = 1.0 \text{ V},$ $I_F = 0.5 \text{ mA}$
t_r, t_f	Rise and Fall Times (Note 2)		80		μs	$V_{IO} = 500 \text{ V}$ $V_{IO} = 0,$ $f = 1.0 \text{ MHz}$ $I_C = 10 \text{ mA},$ $V_{CC} = 10 \text{ V},$ $R_L = 100 \Omega$

Notes

- Isolation voltage defined as minimum of 5 s continuous application.
- Rise time is defined as the time for the collector current to rise from 10% to 90% of peak value. Fall time is defined as the time required for the current to decrease from 90% to 10% of peak value.